Docket No.: 4685
Inv.: Shinsuke FUJIWARA et al.
Title: Semiconductor Light Emitting Device
I of 16

## FIG.1

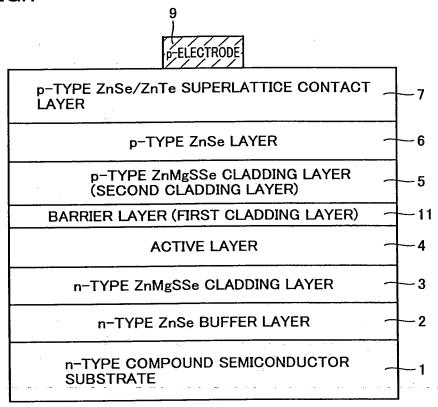


FIG.2

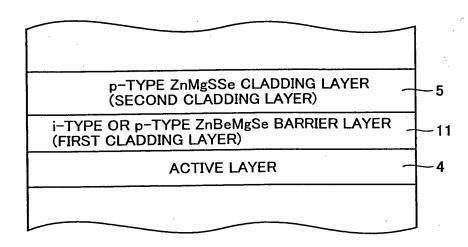


FIG.3

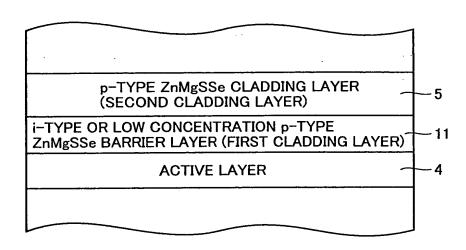
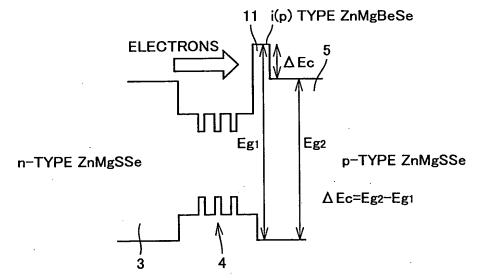
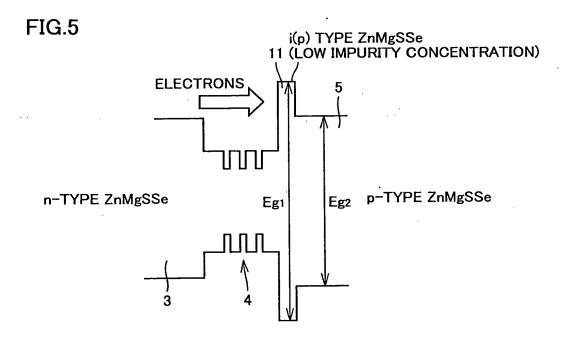
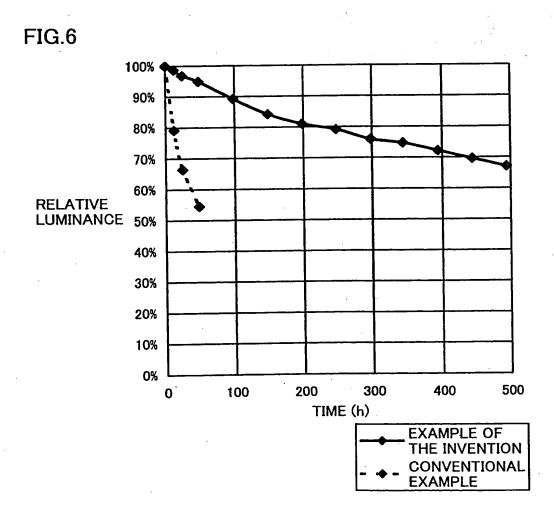


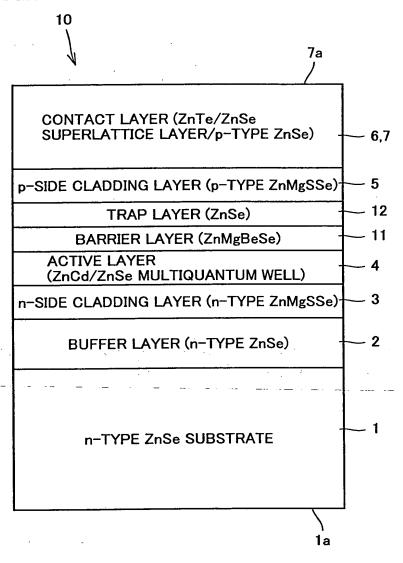
FIG.4











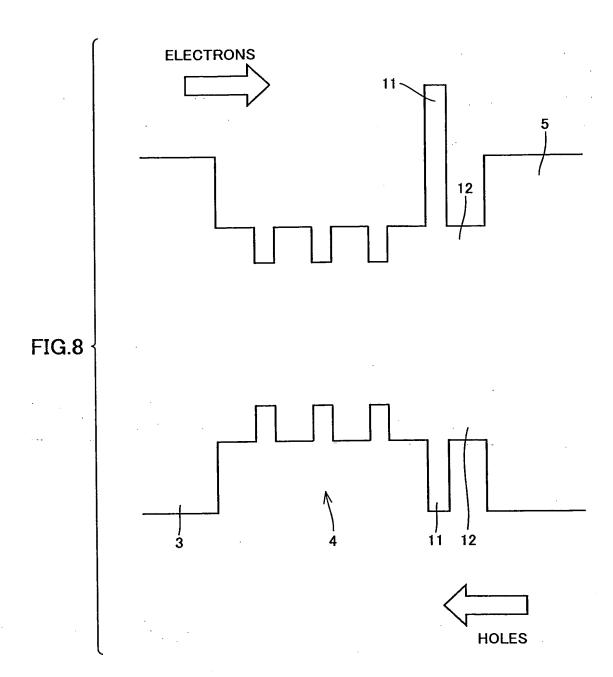


FIG.9

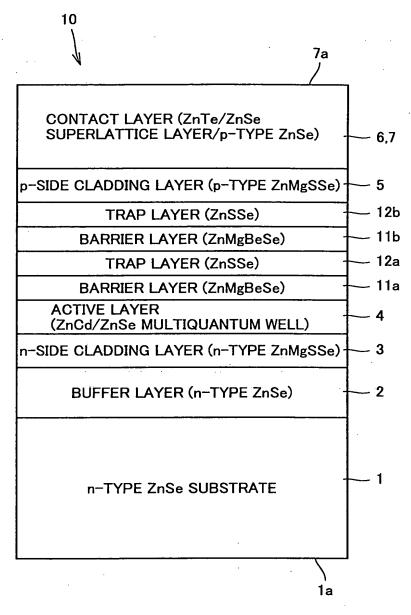
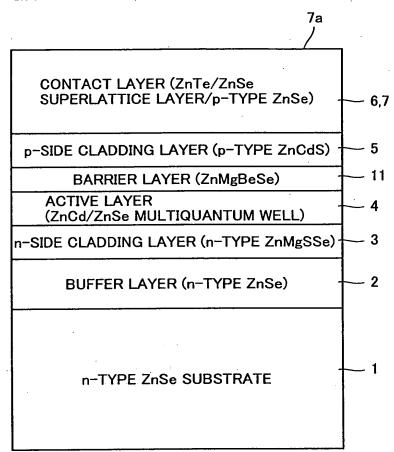
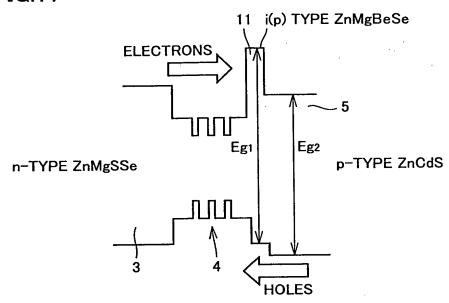
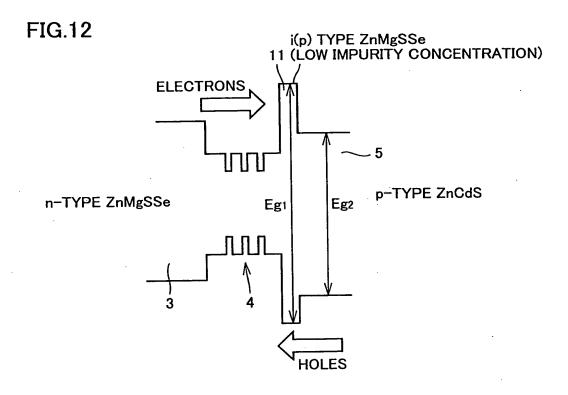


FIG.10



**FIG.11** 



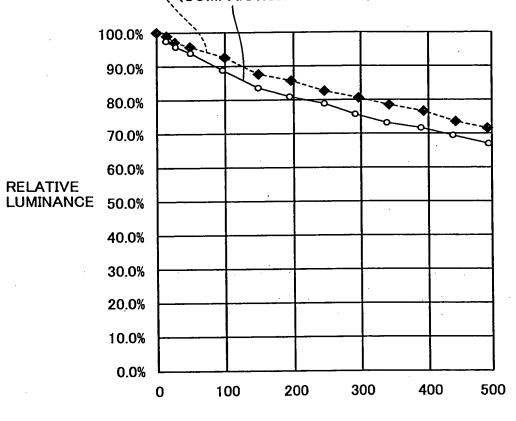


Docket No.: 3685 9 of 16

**FIG.13** 

ZnMgBeSe BARRIER LAYER + p-TYPE ZnCdS CLADDING LAYER (EXAMPLE OF THE INVENTION)

ZnMgSSe BARRIER LAYER + p-TYPE ZnMgSSe CLADDING LAYER (COMPARATIVE EXAMPLE)



TIME (h)

**FIG.14** 

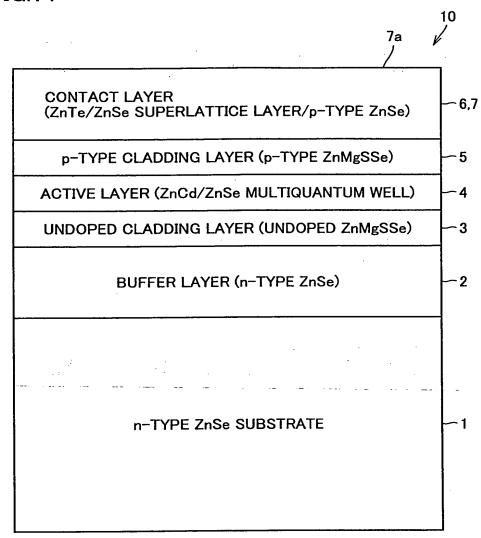


FIG.15

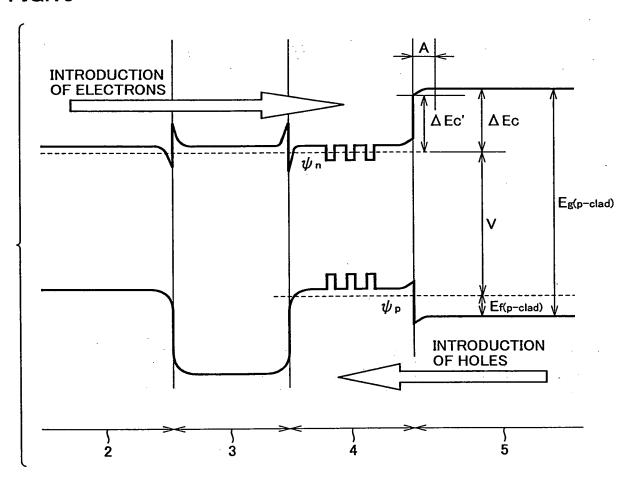
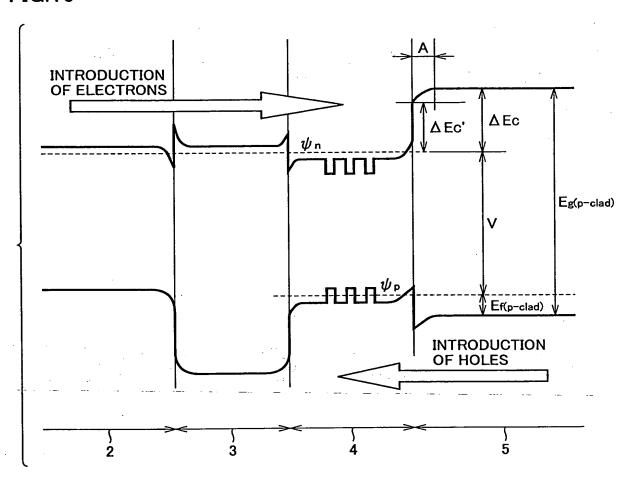


FIG.16



Docket No.: 4685 13 of 16

**FIG.17** 

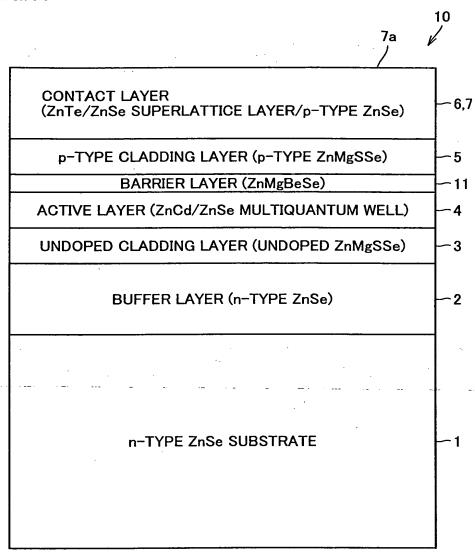
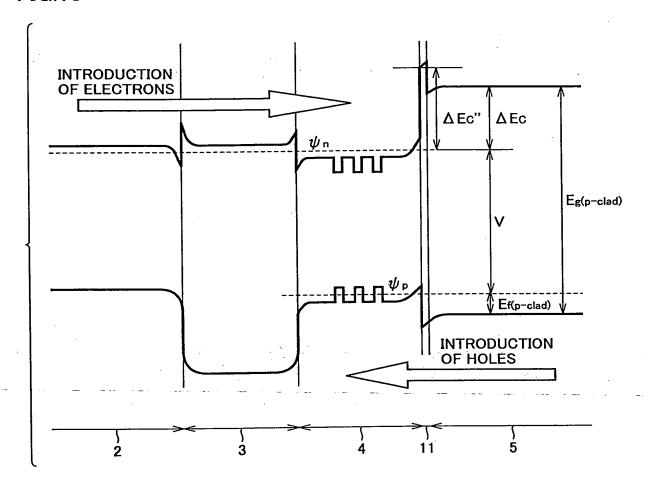
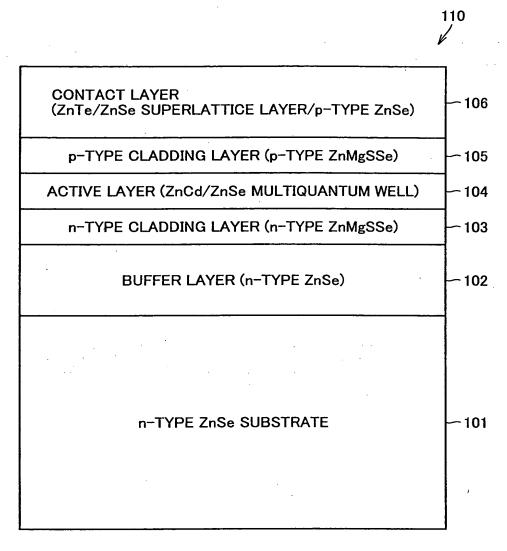


FIG.18



Docket No.: 4685 15 of 16

FIG.19 PRIOR ART



Docket No.: 4685 16 of 16

FIG.20 PRIOR ART

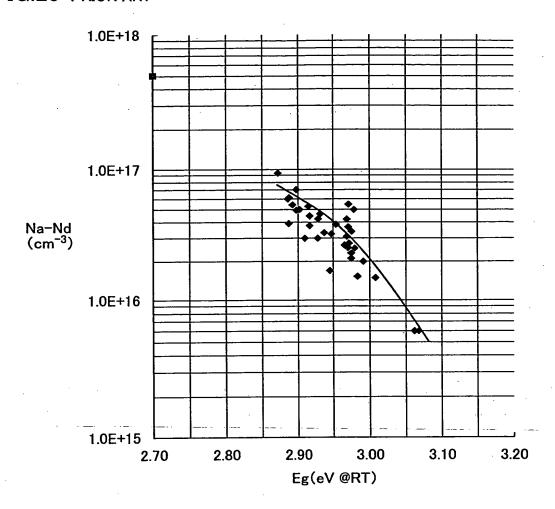
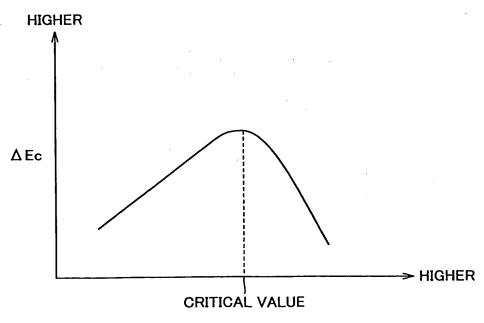


FIG.21 PRIOR ART



BAND GAP Egp OF p-TYPE CLADDING LAYER